# **Dual General Purpose Transistor**

The NST857BDP6T5G device is a spin-off of our popular SOT-23/SOT-323/SOT-563 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-963 six-leaded surface mount package. By putting two discrete devices in one package, this device is ideal for low-power surface mount applications where board space is at a premium.

### **Features**

- h<sub>FE</sub>, 220–475
- Low  $V_{CE(sat)}$ ,  $\leq 0.3 \text{ V}$
- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- This is a Pb-Free Device

#### **MAXIMUM RATINGS**

| Rating                         | Symbol    | Value            | Unit   |      |
|--------------------------------|-----------|------------------|--------|------|
| Collector - Emitter Voltage    |           | $V_{CEO}$        | -45    | Vdc  |
| Collector - Base Voltage       |           | $V_{CBO}$        | -50    | Vdc  |
| Emitter - Base Voltage         |           | V <sub>EBO</sub> | -6.0   | Vdc  |
| Collector Current - Continuous |           | I <sub>C</sub>   | -100   | mAdc |
| Electrostatic Discharge        | HBM<br>MM | ESD<br>Class     | 2<br>B |      |

### THERMAL CHARACTERISTICS

| Characteristic (Single Heated)  | Symbol                            | Max            | Unit        |
|---|-----------------------------------|----------------|-------------|
| Total Device Dissipation T <sub>A</sub> = 25°C Derate above 25°C (Note 1) | P <sub>D</sub>                    | 240<br>1.9     | mW<br>mW/°C |
| Thermal Resistance, Junction-to-Ambient (Note 1)                          | $R_{	heta JA}$                    | 520            | °C/W        |
| Total Device Dissipation T <sub>A</sub> = 25°C Derate above 25°C (Note 2) | P <sub>D</sub>                    | 280<br>2.2     | mW<br>mW/°C |
| Thermal Resistance, Junction-to-Ambient (Note 2)                          | $R_{\theta JA}$                   | 446            | °C/W        |
| Characteristic (Dual Heated) (Note 3)                                     | Symbol                            | Max            | Unit        |
| Total Device Dissipation T <sub>A</sub> = 25°C Derate above 25°C (Note 1) | P <sub>D</sub>                    | 350<br>2.8     | mW<br>mW/°C |
| Thermal Resistance, Junction-to-Ambient (Note 1)                          | $R_{\theta JA}$                   | 357            | °C/W        |
| Total Device Dissipation T <sub>A</sub> = 25°C Derate above 25°C (Note 2) | P <sub>D</sub>                    | 420<br>3.4     | mW<br>mW/°C |
| Thermal Resistance, Junction-to-Ambient (Note 2)                          | $R_{\theta JA}$                   | 297            | °C/W        |
| Junction and Storage Temperature Range                                    | T <sub>J</sub> , T <sub>stg</sub> | -55 to<br>+150 | °C          |

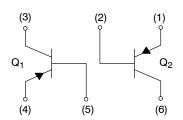
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. FR-4 @ 100 mm², 1 oz. copper traces, still air. 2. FR-4 @ 500 mm², 1 oz. copper traces, still air.
- 3. Dual heated values assume total power is sum of two equally powered channels.



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NST857BDP6T5G



SOT-963 CASE 527AD **PLASTIC** 

#### **MARKING DIAGRAM**



K = Device Code

= Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

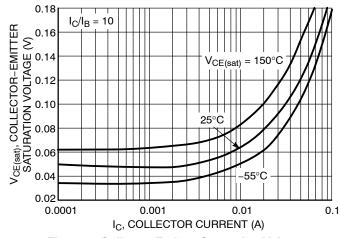
### **ORDERING INFORMATION**

| Device        | Package              | Shipping <sup>†</sup> |
|---------------|----------------------|-----------------------|
| NST857BDP6T5G | SOT-963<br>(Pb-Free) | 8000/Tape & Reel      |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

| Characteristic  | Symbol               | Min       | Тур          | Max            | Unit     |
|---|----------------------|-----------|--------------|----------------|----------|
| OFF CHARACTERISTICS   |                      |           |              |                |          |
| Collector - Emitter Breakdown Voltage (I <sub>C</sub> = -10 mA)   | V <sub>(BR)CEO</sub> | -45       | -            | -              | V        |
| Collector – Emitter Breakdown Voltage ( $I_C = -10 \mu A$ , $V_{EB} = 0$ )  | V <sub>(BR)CES</sub> | -50       | -            | -              | V        |
| Collector – Base Breakdown Voltage (I <sub>C</sub> = –10 μA)  | V <sub>(BR)CBO</sub> | -50       | -            | -              | V        |
| Emitter – Base Breakdown Voltage (I <sub>E</sub> = –1.0 μA)   | V <sub>(BR)EBO</sub> | -5.0      | -            | -              | V        |
| Collector Cutoff Current ( $V_{CB} = -30 \text{ V}$ )<br>( $V_{CB} = -30 \text{ V}$ , $T_A = 150^{\circ}\text{C}$ )                       | I <sub>CBO</sub>     | -<br>-    | -<br>-       | -15<br>-4.0    | nA<br>μA |
| ON CHARACTERISTICS  | ·                    |           |              |                |          |
| DC Current Gain $ (I_C = -10  \mu \text{A, V}_{CE} = -5.0  \text{V}) $ $ (I_C = -2.0  \text{mA, V}_{CE} = -5.0  \text{V}) $               | h <sub>FE</sub>      | -<br>220  | 150<br>290   | -<br>475       | _        |
| Collector – Emitter Saturation Voltage ( $I_C = -10$ mA, $I_B = -0.5$ mA) ( $I_C = -100$ mA, $I_B = -5.0$ mA)                             | V <sub>CE(sat)</sub> | -<br>-    | -<br>-       | -0.3<br>-0.7   | V        |
| Base – Emitter Saturation Voltage ( $I_C$ = -10 mA, $I_B$ = -0.5 mA) ( $I_C$ = -100 mA, $I_B$ = -5.0 mA)                                  | V <sub>BE(sat)</sub> | -<br>-    | -0.7<br>-0.9 | -<br>-         | V        |
| Base – Emitter On Voltage<br>( $I_C$ = -2.0 mA, $V_{CE}$ = -5.0 V)<br>( $I_C$ = -10 mA, $V_{CE}$ = -5.0 V)                                | V <sub>BE(on)</sub>  | -0.6<br>- | -<br>-       | -0.75<br>-0.82 | V        |
| SMALL-SIGNAL CHARACTERISTICS  |                      |           |              |                |          |
| Current – Gain – Bandwidth Product ( $I_C = -10$ mA, $V_{CE} = -5.0$ Vdc, $f = 100$ MHz)  | f <sub>T</sub>       | 100       | _            | -              | MHz      |
| Output Capacitance<br>(V <sub>CB</sub> = -10 V, f = 1.0 MHz)  | C <sub>obo</sub>     | -         | -            | 4.5            | pF       |
| Input Capacitance<br>(V <sub>EB</sub> = -0.5 V, f = 1.0 MHz)  | C <sub>ibo</sub>     | _         | _            | 10             | pF       |
| Noise Figure (I <sub>C</sub> = $-0.2$ mA, V <sub>CE</sub> = $-5.0$ Vdc, R <sub>S</sub> = $2.0$ k $\Omega$ , f = $1.0$ kHz, BW = $200$ Hz) | NF                   | _         | _            | 10             | dB       |





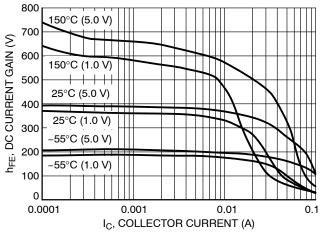


Figure 2. DC Current Gain vs. Collector Current

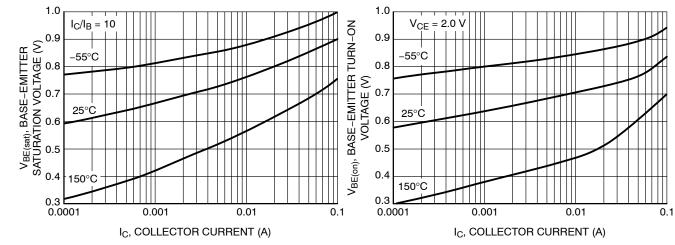


Figure 3. Base Emitter Saturation Voltage vs.
Collector Current

Figure 4. Base Emitter Turn-On Voltage vs. Collector Current

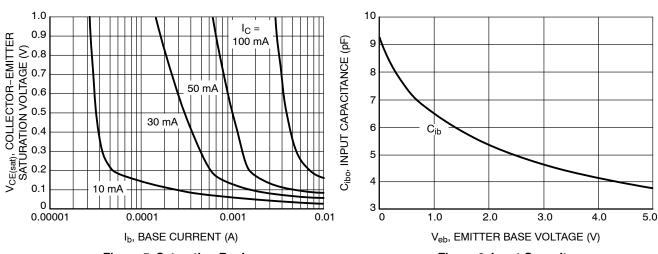


Figure 5. Saturation Region

Figure 6. Input Capacitance

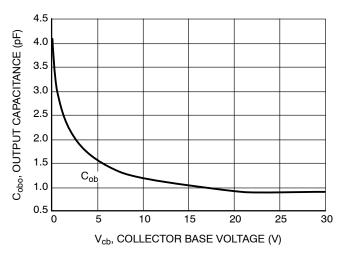
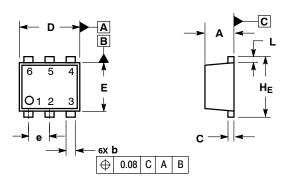


Figure 7. Output Capacitance

### PACKAGE DIMENSIONS

### SOT-963 CASE 527AD-01 ISSUE B

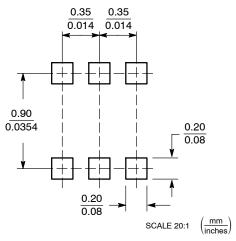


#### NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETERS
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

|     | MILLIMETERS |      |      | INCHES   |       |       |
|-----|-------------|------|------|----------|-------|-------|
| DIM | MIN         | NOM  | MAX  | MIN      | MOM   | MAX   |
| Α   | 0.34        | 0.37 | 0.40 |          |       |       |
| b   | 0.10        | 0.15 | 0.20 | 0.004    | 0.006 | 0.008 |
| С   | 0.07        | 0.12 | 0.17 | 0.003    | 0.005 | 0.007 |
| D   | 0.95        | 1.00 | 1.05 | 0.037    | 0.039 | 0.041 |
| E   | 0.75        | 0.80 | 0.85 | 0.03     | 0.032 | 0.034 |
| е   | 0.35 BSC    |      | (    | 0.014 BS | Ö     |       |
| L   | 0.05        | 0.10 | 0.15 | 0.002    | 0.004 | 0.006 |
| HE  | 0.95        | 1.00 | 1.05 | 0.037    | 0.039 | 0.041 |

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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